

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. – 12. (Cancelled)

13. (Currently Amended) A semiconductor device comprising:
 - a semiconductor substrate;
 - a gate electrode formed on said semiconductor substrate;
 - a diffusion layer formed within said semiconductor substrate and corresponding to said gate electrode;
 - a connection layer disposed above said gate electrode through an insulating layer; and
 - a plug connected electrically with said connection layer and said diffusion layer,
 - wherein said plug comprises a main conductive film and an adjacent conductive film disposed outside of said main conductive film, and
 - said main conductive film includes copper as a main constituent element, and
 - said adjacent conductive film includes as a main constituent element at least one element selected from a group consisting of ~~rhodium~~, ruthenium, iridium, and osmiumand platinum.

14. (Currently Amended) A semiconductor device according to Claim 13 comprising:

a semiconductor substrate;
a gate electrode formed on said semiconductor substrate;
a diffusion layer formed within said semiconductor substrate and corresponding to said gate electrode;
a connection layer disposed above said gate electrode through an insulating layer; and
a plug connected electrically with said connection layer and said diffusion layer,
wherein said plug comprises a main conductive film and an adjacent conductive film disposed outside of said main conductive film, and
said main conductive film includes copper as a main constituent element,
said adjacent conductive film includes as a main constituent element at least one element selected from a group consisting of rhodium, ruthenium, iridium, and osmium and platinum, wherein said adjacent conductive film includes as an added constituent element at least one element selected from a group consisting of palladium, cobalt, nickel and titanium.

15. (Currently Amended) A semiconductor device according to Claim 1314, wherein said adjacent conductive film includes as ansaid added constituent element with said at least one element selected from a group consisting of palladium, cobalt, nickel and titanium with a concentration of not less than 0.14 at.% and not more than 25 at.%.

16. (Currently Amended) A semiconductor device comprising:

- a semiconductor substrate;
- a gate electrode formed on said semiconductor substrate;
- a diffusion layer formed within said semiconductor substrate and corresponding to said gate electrode;
- a connection layer disposed above said gate electrode through an insulating layer; and
- a plug connected electrically with said connection layer and said diffusion layer,

wherein said connection layer comprises a main conductive film and an adjacent conductive film disposed outside of said main conductive film, and

 said main conductive film includes copper as a main constituent element, and

 said adjacent conductive film includes as a main constituent element at least one element selected from a group consisting of rhodium, ruthenium, iridium, and osmium-and platinum.

17. (Currently Amended) A semiconductor device according to Claim 16 comprising:

- a semiconductor substrate;
- a gate electrode formed on said semiconductor substrate;
- a diffusion layer formed within said semiconductor substrate and corresponding to said gate electrode;
- a connection layer disposed above said gate electrode through an insulating layer; and

a plug connected electrically with said connection layer and said diffusion layer,

wherein said connection layer comprises a main conductive film and an adjacent conductive film disposed outside of said main conductive film, and

said main conductive film includes copper as a main constituent element, and
said adjacent conductive film includes as a main constituent element at least one
element selected from a group consisting of rhodium, ruthenium, iridium, osmium
and platinum, wherein said adjacent conductive film includes as an added
constituent element at least one element selected from a group consisting of
palladium, cobalt, nickel and titanium.

18. (Currently Amended) A semiconductor device according to Claim 1617,
wherein said adjacent conductive film includes as ansaid added constituent element
withsaid at least one element selected from a group consisting of palladium, cobalt,
nickel and titanium with a concentration of not less than 0.14 at.% and not more than
25 at.%.

19. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
a gate electrode formed on said semiconductor substrate;
a diffusion layer formed within said semiconductor substrate and
corresponding to said gate electrode;
a connection layer disposed above said gate electrode through an insulating
layer; and

a plug connected electrically with said connection layer and said gate electrode,

wherein said plug includes copper as a main constituent element, and said gate electrode includes as a main constituent element at least one element selected from a group consisting of rhodium, ruthenium, iridium, osmium and platinum.

20. (Currently Amended) A semiconductor device according to Claim 19 comprising:

a semiconductor substrate;

a gate electrode formed on said semiconductor substrate;

a diffusion layer formed within said semiconductor substrate and corresponding to said gate electrode;

a connection layer disposed above said gate electrode through an insulating layer; and

a plug connected electrically with said connection layer and said gate electrode,

wherein said plug includes copper as a main constituent element, and said gate electrode includes as a main constituent element at least one element selected from a group consisting of rhodium, ruthenium, iridium, osmium and platinum,
wherein said gate electrode includes as an added constituent element at least one element selected from a group consisting of palladium, cobalt, nickel and titanium.

21. (Currently Amended) A semiconductor device according to Claim 1920, wherein said gate electrode includes as ansaid added constituent element with said

at least one element selected from a group consisting of palladium, cobalt, nickel and titanium with a concentration of not less than 0.14 at.% and not more than 25 at.%.

22. (Currently Amended) A semiconductor device comprising:

 a semiconductor substrate;

 a gate electrode formed on said semiconductor substrate;

 a diffusion layer formed within said semiconductor substrate and corresponding to said gate electrode;

 a connection layer disposed above said gate electrode through an insulating layer; and

 a plug connected electrically with said connection layer and said gate electrode,

 wherein said plug includes copper as a main constituent element, and said gate electrode includes a first conductive film and a second conductive film disposed at a position nearer to said plug than said first conductive film, and

 said first conductive film includes silicon, and

 said second conductive film includes as a main constituent element at least one element selected from a group consisting of rhodium, ruthenium, iridium, osmium and platinum.

23. (Currently Amended) A semiconductor device according to Claim 22 comprising:

a semiconductor substrate;

a gate electrode formed on said semiconductor substrate;
a diffusion layer formed within said semiconductor substrate and
corresponding to said gate electrode;
a connection layer disposed above said gate electrode through an insulating
layer; and
a plug connected electrically with said connection layer and said gate
electrode,
wherein said plug includes copper as a main constituent element, and said
gate electrode includes a first conductive film and a second conductive film disposed
at a position nearer to said plug than said first conductive film, and
said first conductive film includes silicon, and
said second conductive film includes as a main constituent element at least
one element selected from a group consisting of rhodium, ruthenium, iridium,
osmium and platinum, wherein said second conductive film includes as an added
constituent element at least one element selected from a group consisting of
palladium, cobalt, nickel and titanium.

24. (Currently Amended) A semiconductor device according to Claim 2223,
wherein said second conductive film includes ~~as-ansaid~~ added constituent element
with said at least one element selected from a group consisting of palladium, cobalt,
nickel and titanium with a concentration of not less than 0.14 at.% and not more than
25 at.%.